

**CLAIM SUMMARY DOCUMENT**

1. (Original) A reactive ion etching (RIE) method performed to pass through a silicon layer on a sequentially-stacked structure of the silicon layer, an insulating layer and a silicon substrate, the method comprising the steps of:

- (a) forming an insulating layer on a silicon substrate;
- (b) forming trenches on the insulating layer to expose the silicon substrate;
- (c) forming a silicon layer on the insulating layer to fill the trenches; and
- (d) patterning the silicon layer to form first etch regions, which pass through the silicon layer, to include the trenches.

2. (Original) The RIE method of claim 1, wherein step (d) comprises patterning the silicon layer positioned between trenches to form second etch regions which are narrower than the first etch regions.

3. (Original) The RIE method of claim 1, wherein step (d) comprises removing silicon filled in the trenches to expose the silicon substrate.

4. (New) A reactive ion etching (RIE) method performed to pass through a silicon layer on a sequentially-stacked structure of the silicon layer, an insulating layer and a silicon substrate, the method comprising the steps of:

- (a) forming an insulating layer on a silicon substrate;

- (b) forming trenches on the insulating layer to expose a top surface of the silicon substrate;
- (c) forming a silicon layer on the insulating layer to fill the trenches; and
- (d) patterning the silicon layer to form first etch regions, which pass through the silicon layer, to include the trenches.

5. (New) The RIE method of claim 4, wherein step (d) comprises patterning the silicon layer positioned between trenches to form second etch regions which are narrower than the first etch regions.

6. (New) The RIE method of claim 4, wherein step (d) comprises removing silicon filled in the trenches to expose the silicon substrate.